

**IN THE SPECIFICATION:**

Please cancel the amendment to the specification in the amendment of March 19, 2009. Accordingly, the paragraph at page 19, line 22 – page 20, line 6 should now read as follows (without the prior amendment):

After that, in order to improve the contact property, plasma of oxygen, nitrogen, helium or the like is irradiated by drop discharge means 13 having plural plasma irradiating ports and composition discharge ports arrayed in a uniaxial direction, and then a resist composition is selectively discharged to form a mask pattern 14 for forming a gate electrode on the conductive film 11, as shown in Fig.8(B). In this case, since the drop discharge means has the discharge ports arrayed only in a uniaxial direction, it suffices to operate heads only at required positions (13a). To process the entire surface of the substrate, one or both of the substrate 10 and the plasma processing means and drop discharge means 13 may be moved. Such processing is similarly performed in the following steps.